



## 49A, 55V, 0.024 Ohm, N-Channel UltraFET Power MOSFETs

These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Formerly developmental type TA75329.

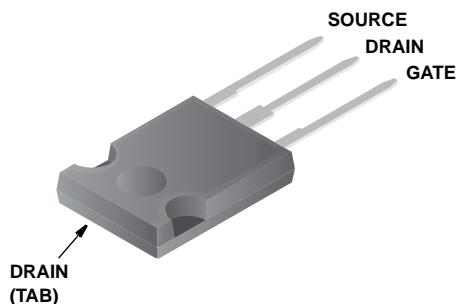
### Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75329G3	TO-247	75329G
HUF75329P3	TO-220AB	75329P
HUF75329S3S	TO-263AB	75329S

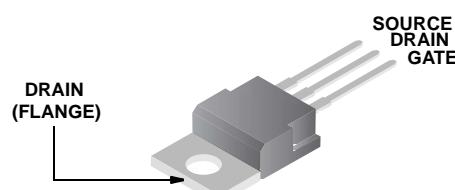
NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUF75329S3ST.

### Packaging

JEDEC STYLE TO-247



JEDEC TO-220AB



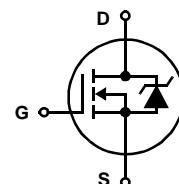
JEDEC TO-263AB



### Features

- 49A, 55V
- Ultra Low On-Resistance,  $r_{DS(ON)} = 0.024\Omega$
- Temperature Compensating PSPICE® and SABER™ Models
  - Available on the web at: [www.fairchildsemi.com](http://www.fairchildsemi.com)
- Thermal Impedance PSPICE and SABER Models
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
  - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

### Symbol



# HUF75329G3, HUF75329P3, HUF75329S3SOGM

## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

			UNITS
Drain to Source Voltage (Note 1) . . . . .	$V_{DSS}$	55	V
Drain to Gate Voltage ( $R_{GS} = 20\text{k}\Omega$ ) (Note 1) . . . . .	$V_{DGR}$	55	V
Gate to Source Voltage . . . . .	$V_{GS}$	$\pm 20$	V
Drain Current			
Continuous (Figure 2) . . . . .	$I_D$	49	A
Pulsed Drain Current . . . . .	$I_{DM}$	Figure 4	
Pulsed Avalanche Rating . . . . .	$E_{AS}$	Figures 6, 14, 15	
Power Dissipation . . . . .	$P_D$	128	W
Derate Above $25^\circ\text{C}$ . . . . .		0.86	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature . . . . .	$T_J, T_{STG}$	-55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s. . . . .	$T_L$	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334 . . . . .	$T_{pkg}$	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTE:

1.  $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ .

## Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
<b>OFF STATE SPECIFICATIONS</b>							
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$	
		$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}, T_C = 150^\circ\text{C}$	-	-	250	$\mu\text{A}$	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA	
<b>ON STATE SPECIFICATIONS</b>							
Gate to Source Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V	
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 49\text{A}, V_{GS} = 10\text{V}$ (Figure 9)	-	0.020	0.024	$\Omega$	
<b>THERMAL SPECIFICATIONS</b>							
Thermal Resistance Junction to Case	$R_{\theta JC}$	(Figure 3)	-	-	1.17	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247	-	-	30	$^\circ\text{C}/\text{W}$	
		TO-220, TO-263	-	-	62	$^\circ\text{C}/\text{W}$	
<b>SWITCHING SPECIFICATIONS (<math>V_{GS} = 10\text{V}</math>)</b>							
Turn-On Time	$t_{ON}$	$V_{DD} = 30\text{V}, I_D \approx 49\text{A}, R_L = 0.61\Omega, V_{GS} = 10\text{V}, R_{GS} = 9.1\Omega$	-	-	105	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	12	-	ns	
Rise Time	$t_r$		-	58	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	33	-	ns	
Fall Time	$t_f$		-	33	-	ns	
Turn-Off Time	$t_{OFF}$		-	-	100	ns	
<b>GATE CHARGE SPECIFICATIONS</b>							
Total Gate Charge	$Q_g(TOT)$	$V_{GS} = 0\text{V}$ to $20\text{V}$	$V_{DD} = 30\text{V}, I_D \approx 49\text{A}, R_L = 0.61\Omega, I_g(\text{REF}) = 1.0\text{mA}$ (Figure 13)	-	60	75	nC
Gate Charge at 10V	$Q_g(10)$	$V_{GS} = 0\text{V}$ to $10\text{V}$		-	35	43	nC
Threshold Gate Charge	$Q_g(TH)$	$V_{GS} = 0\text{V}$ to $2\text{V}$		-	2.0	2.5	nC
Gate to Source Gate Charge	$Q_{gs}$			-	5	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$			-	13	-	nC

# HUF75329G3, HUF75329P3, HUF75329S3S

**Electrical Specifications**  $T_C = 25^{\circ}\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>CAPACITANCE SPECIFICATIONS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	1060	-	pF
Output Capacitance	$C_{OSS}$	(Figure 12)	-	405	-	pF
Reverse Transfer Capacitance	$C_{RSS}$		-	95	-	pF

## Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	$I_{SD} = 49\text{A}$	-	-	1.25	V
Reverse Recovery Time	$t_{rr}$	$I_{SD} = 49\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	72	ns
Reverse Recovered Charge	$Q_{RR}$	$I_{SD} = 49\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	120	nC

## Typical Performance Curves

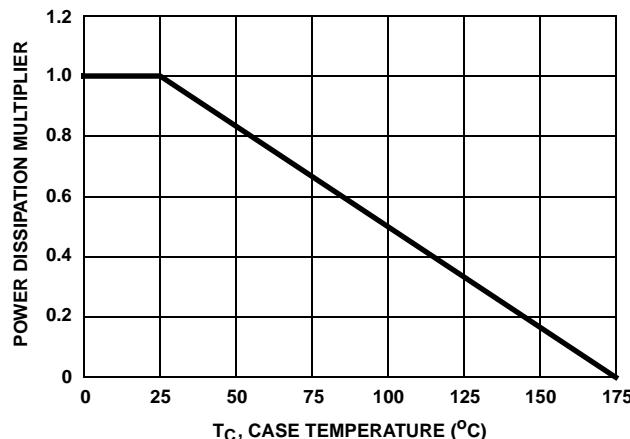


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

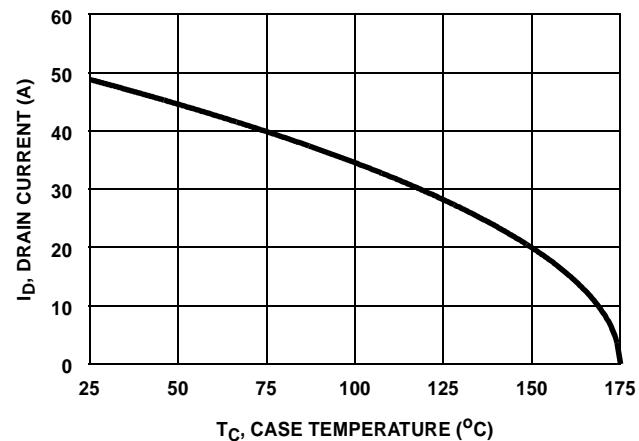


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

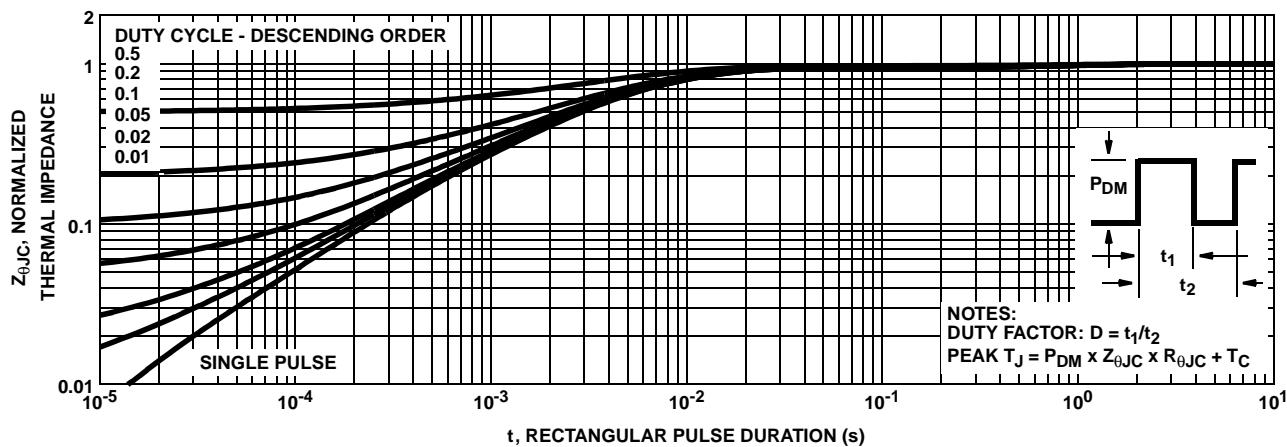


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE